

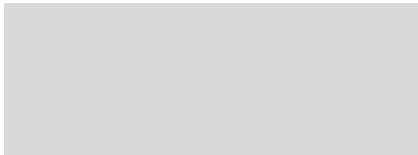


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	°C					
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6

FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

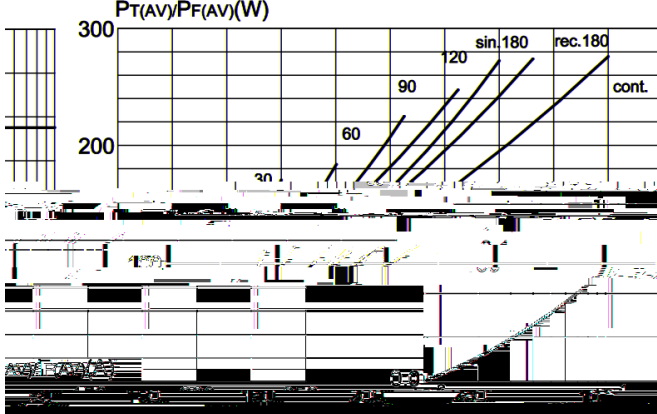


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

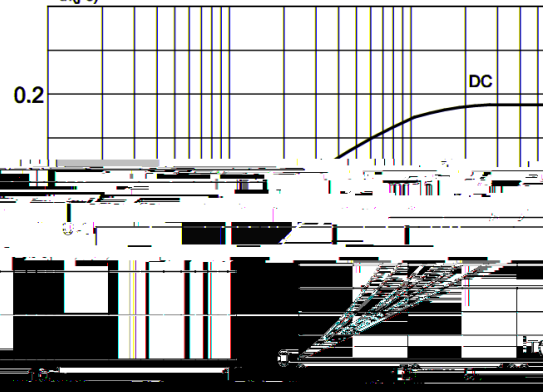


FIG.5 Gate trigger characteristics

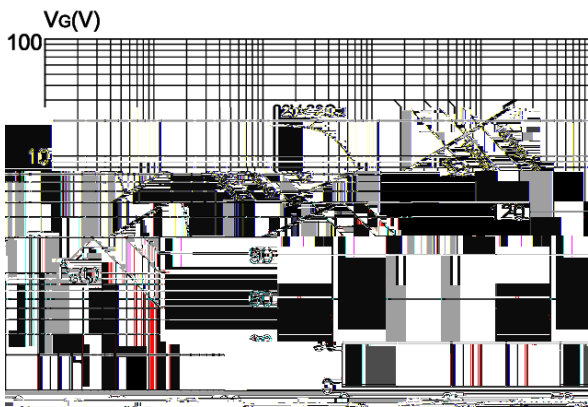
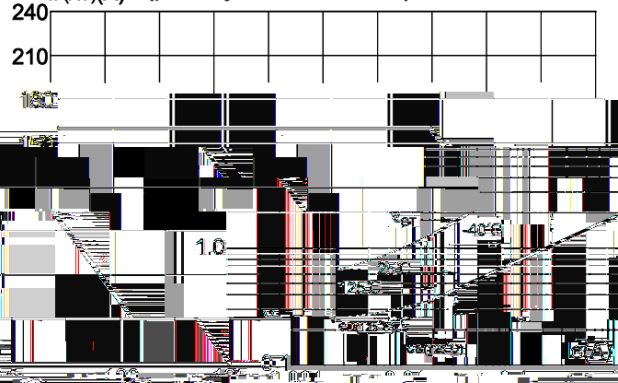
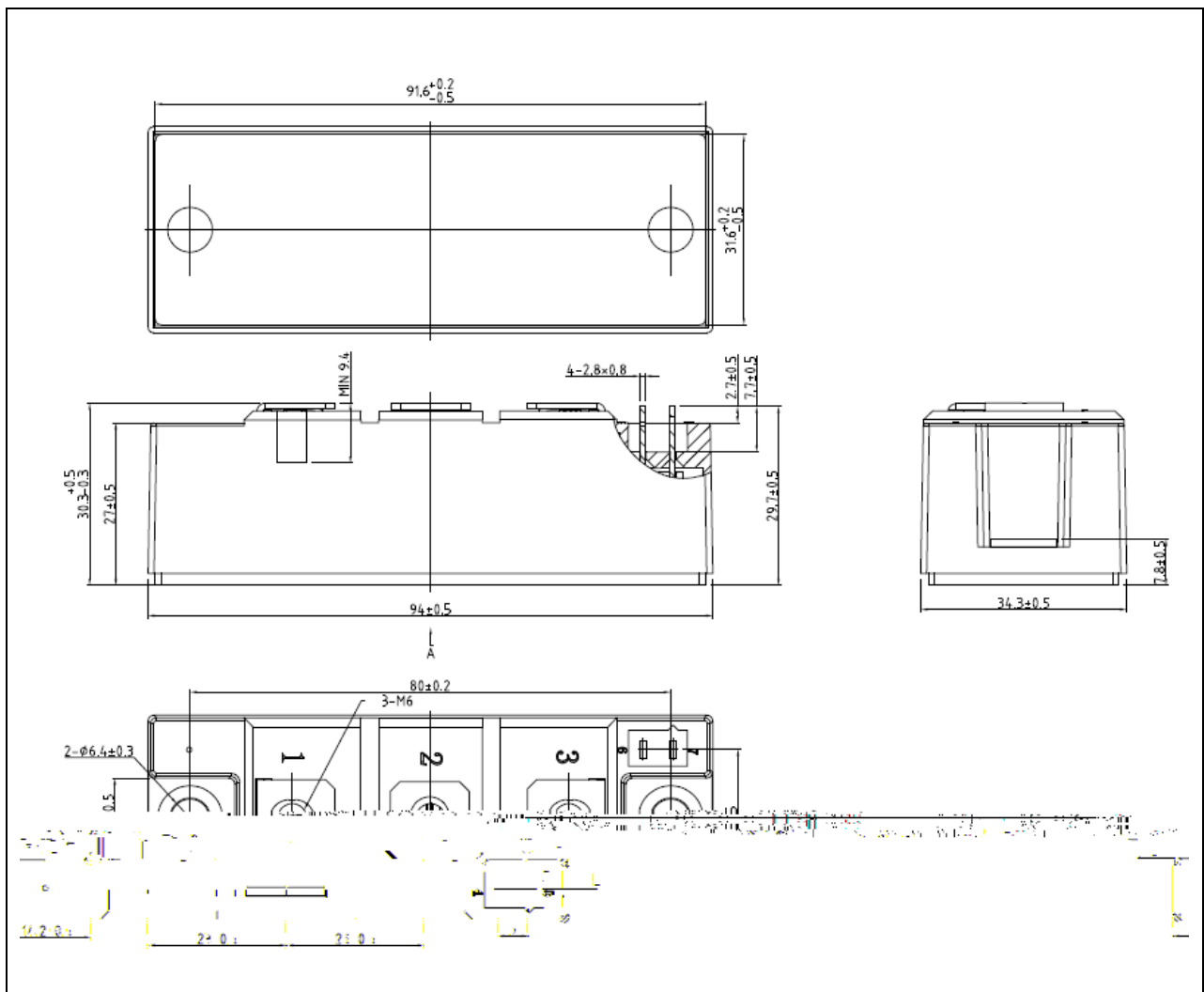
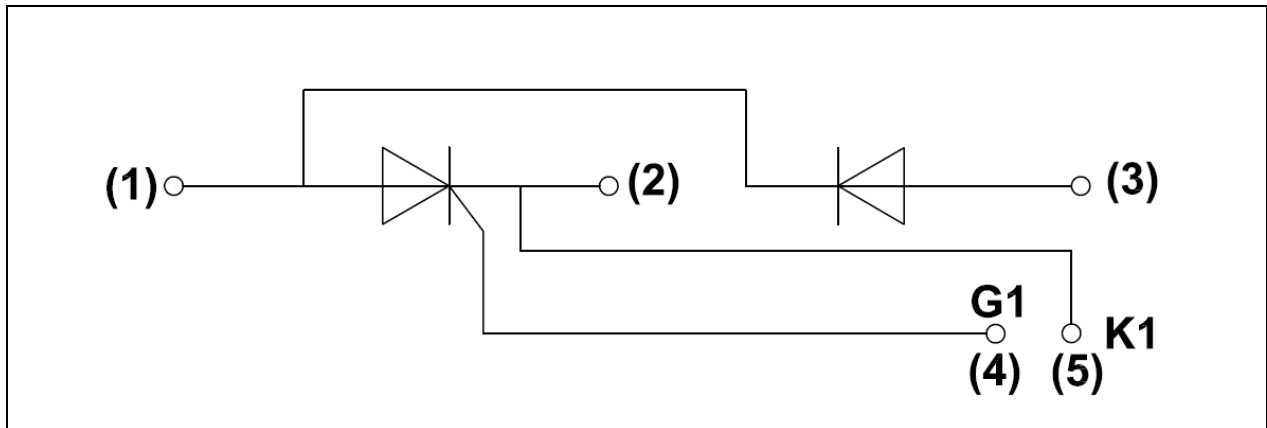


FIG.6: Forward current vs. case temperature
(per thyristor or diode)







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